

# 1S2074(H)

Silicon Epitaxial Planar Diode for High Speed Switching

# HITACHI

ADE-208-142A (Z)

Rev. 1

Aug. 1995

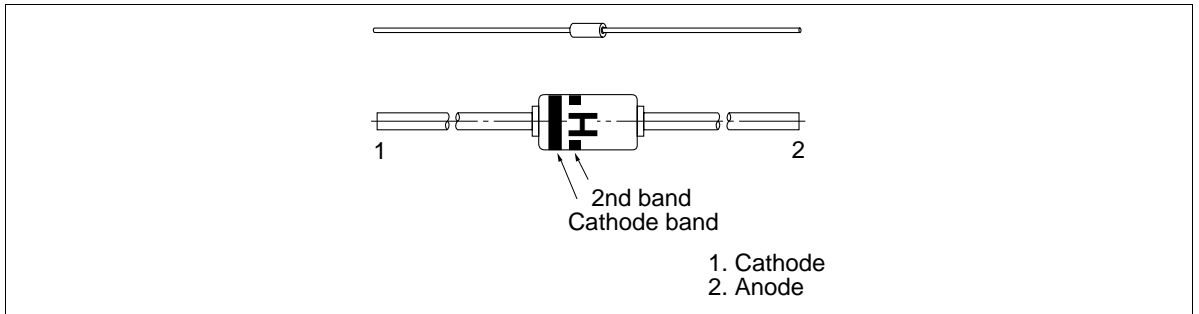
## Features

- Low capacitance. ( $C = 3.0\text{pF max}$ )
- Short reverse recovery time. ( $t_{rr} = 4.0\text{ns max}$ )
- High reliability with glass seal.

## Ordering Information

Type No.	Cathode	2nd band	Mark	Package Code
1S2074(H)	Green	White	H	DO-35

## Outline



**Absolute Maximum Ratings** ( $T_a = 25^\circ\text{C}$ )

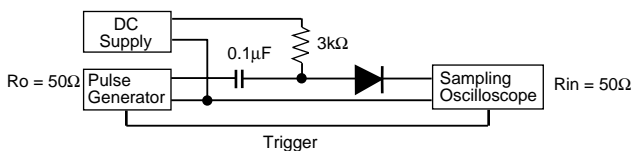
Item	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}$	50	V
Reverse voltage	$V_R$	45	V
Peak forward current	$I_{FM}$	450	mA
Non-Repetitive peak forward surge current	$I_{FSM}^*$	600	mA
Average forward current	$I_O$	150	mA
Power dissipation	$P_d$	250	mW
Junction temperature	$T_j$	175	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-65 to +175	$^\circ\text{C}$

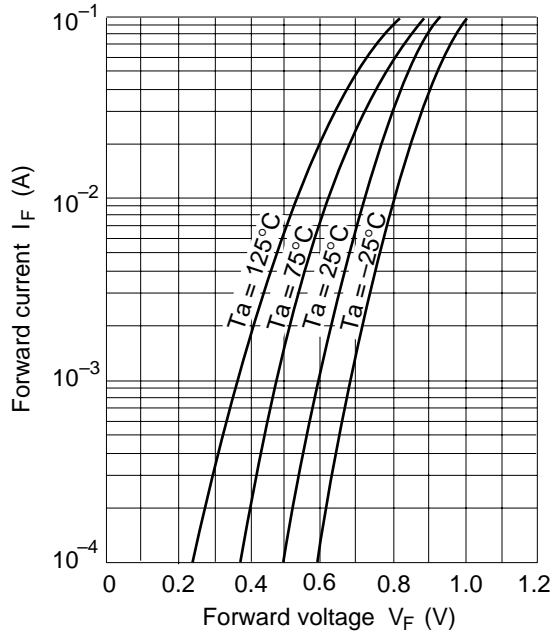
Note: Within 1s forward surge current.

**Electrical Characteristics** ( $T_a = 25^\circ\text{C}$ )

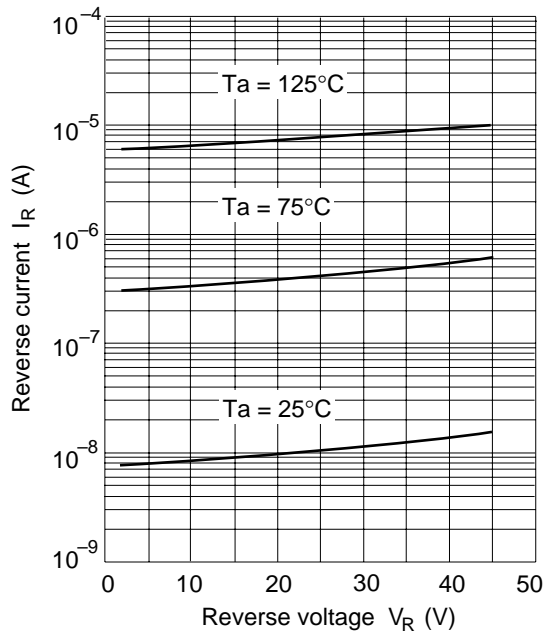
Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_F$	0.64	—	0.8	V	$I_F = 10\text{mA}$
Reverse current	$I_R$	—	—	0.1	$\mu\text{A}$	$V_R = 30\text{V}$
Capacitance	$C$	—	—	3.0	pF	$V_R = 1\text{V}, f = 1\text{MHz}$
Reverse recovery time	$t_{rr}^*$	—	—	4.0	ns	$I_F = I_R = 10\text{mA}, I_{rr} = 1\text{mA}$

Note: Reverse recovery time test circuit





**Fig.1 Forward current Vs. Forward voltage**



**Fig.2 Reverse current Vs. Reverse voltage**

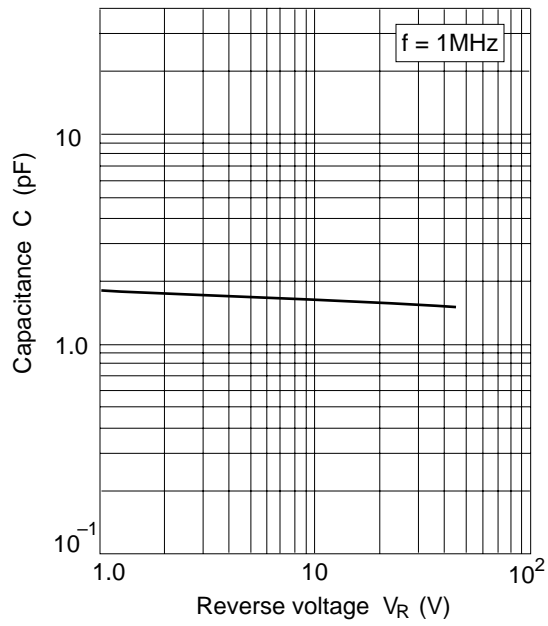
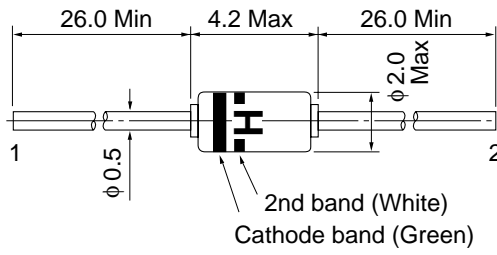


Fig.3 Capacitance Vs. Reverse voltage

Package Dimensions

Unit: mm



1 Cathode  
2 Anode

HITACHI Code	DO-35
JEDEC Code	DO-35
EIAJ Code	SC-48
Weight (g)	0.13

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